

WHAT IS CLAIMED IS:

1. A polishing method which is part of a method for fabricating a semiconductor device, the fabrication method including the process step of polishing a substrate using CMP,

5 wherein in the polishing process step, a tube-type slurry supply pump is used for supplying a slurry, and

wherein in the tube-type slurry supply pump, a vinyl chloride type tube is used as a tube for supplying the slurry.

10 2. The polishing method of claim 1, wherein the vinyl chloride type tube substantially does not contain fine particles for reinforcing the strength of the tube.

3. A polishing method which is part of a method for fabricating a semiconductor device, the fabrication method including the process step of polishing a substrate using
15 CMP,

wherein in the polishing process step, a tube-type slurry supply pump is used for supplying a slurry, and

wherein in the tube-type slurry supply pump, a tube including the inner surface formed of a vinyl chloride type tube and the outer surface formed of a rubber type tube is
20 used as a tube for supplying the slurry.

4. The polishing method of claim 3, wherein the vinyl chloride type tube substantially does not contain fine particles for reinforcing the strength of the tube.

25 5. A polishing method which is part of a method for fabricating a semiconductor

device, the fabrication method including the process step of polishing a substrate using CMP,

wherein in the polishing process step, a tube-type slurry supply pump is used for supplying a slurry, and

5 wherein a filter for removing aggregate particles and a foreign substance contained in the slurry is disposed downstream of the slurry supply pump.

6. The polishing method of claim 5, wherein in the tube-type slurry supply pump, a tube in which at least the inner surface is formed of a vinyl chloride material is used as a
10 tube for supplying the slurry.

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7. A polishing method which is part of a method for fabricating a semiconductor device, the fabrication method including the process step of polishing a substrate using CMP,

15 wherein in the polishing process step, a tube-type slurry supply pump is used for supplying a slurry, and

wherein in the tube-type slurry supply pump, a tube which substantially does not contain fine particles for reinforcing the strength of the tube is used as a tube for supplying the slurry.

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8. The polishing method of claim 7, wherein the tube is a vinyl chloride type tube or a silicon rubber type tube.

9. A method for fabricating a semiconductor device, comprising the polishing
25 method of any one of claims 1 through 8.

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10. A system for polishing a substrate using CMP, comprising:
a CMP apparatus for polishing the substrate; and
a tube-type slurry supply pump for supplying a slurry during polishing,
5 wherein a tube for the tube-type slurry supply pump is a tube in which at least the
inner surface is formed of a vinyl chloride material.

11. The polishing system of claim 10, wherein the tube has a two-layer structure,
and
10 wherein the inner surface of the tube is formed of a vinyl chloride material and the
outer surface of the tube is formed of a rubber material.

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12. A system for polishing a substrate using CMP, comprising:
a CMP apparatus for polishing the substrate;
15 a slurry supply apparatus for supplying a slurry to the CMP apparatus;
a pipe for connecting the slurry supply apparatus and the CMP apparatus; and
a tube-type slurry supply pump disposed in part of the pipe,
wherein a filter for removing at least aggregate particles or a foreign substance
contained in the slurry is disposed between the tube-type slurry supply pump and the CMP
20 apparatus.

13. The polishing system of claim 12, wherein a tube for the tube-type slurry
supply pump is a tube in which at least the inner surface is formed of a vinyl chloride
material.

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14. A system for polishing a substrate using CMP, comprising:
a CMP apparatus for polishing the substrate; and
a tube-type slurry supply pump for supplying a slurry during polishing,
wherein a tube for the tube-type slurry supply pump substantially does not contain
5 fine particles for reinforcing the strength of the tube.